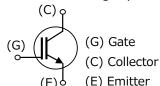


PRELIMINARY

Power Semiconductor IGBT (Insulated Gate Bipolar Transistor)

MR-Series 650V / 30A HighSpeed



MMJ6530C00**

Outline

IGBT (Bare chip) utilizes various technologies that we cultivated by analog semiconductor device production and is the product which prepared a lineup of the wide high voltage, high current which can contribute to high efficiency and saving energy.

Applications

- ·Industrial Motor Drivers
- Inverter
- Welding
- ·UPS

Features © Field St

- ① Field Stop Trench gate IGBT
- 2 Low Collector-Emitter saturation voltage
- 3 High short circuit capability
- 4 Low swiching losses

Absolute Maximum Ratings

Tj=25deg unless otherwise noted.

Parameter	Symbol	Rating	Unit
Collector-Emitter voltage	VCES	650	V
Gate-Emitter voltage	VGES	±30	V
Collector current *1)	IC	30	Α
Junction temperature	Tj	-40~+150	$^{\circ}$

Die Specification

Item	Value	Unit
Die thickness	86	μm
Die size	3.6x3.6(12.96)	mm
Front metal(AlSi)	6.5	μm
Backside metal(AlSi/Ti/Ni/Au)	1.25	μm

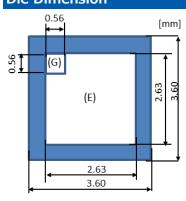
^{*1)}Collector current is limited by Tj(max) and thermal properties of assembly.

Electrical Characteristics

Tj=25deg unless otherwise noted.

Parameter	Symbol	Specification		Unit	condition		
	3,111501	Min	Тур	Max	3.110	55.74.65.7	
Zero gate voltage collector current	ICES	ı	-	1	μΑ	Vce=650V,Vge=0V	
Gate-Emitter leakage current	IGES	ı	-	±100	nA	Vge=±30V,Vce=0V	
Gate-emitter threshold voltage	VGE(th)	4.5	-	6.5	V	Vce=10V,Ic=1.0mA	
Collecter-Emitter saturation voltage	VCE (sat)	-	1.8	2.1	٧	Ic=30A,Vge=15V	
Input capacitance	Cies	-	1100	-	pF	VCE=25V,VGE=0V,	
Reverse transfer capcitance	Cres	-	55	-	pF	f=100kHz	
	td(on)	ı	50	-	ns	Vcc=330V,Ic=30A	
Switching time	tr	ı	45	-	ns	VGE=15/0V,Tj=150℃	
*Reference characteristics	td(off)	-	320	-	ns	Rg(on/off)= $12\Omega/41\Omega$,	
	tf	ı	60	-	ns	Inductive load	
Short circuit withstand time	Tsc	5	-	-	μs	Vcc=400V,Vge=15V,Tj=150℃	

Die Dimension



This characteristic is when it is incorporated in a mold package or evaluation board.

Depending on the assembly conditions etc., it may not be satisfied. Please note that it is not a guaranteed value.

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- The details listed here are not a guarantee of the individual products at the time of ordering.
- When using the products, you will be asked to check their specifications.